

Applicant: Ishiduka et al.
Application No.: Unassigned
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Docket No.: 1608-7 PCT/US
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Amendments to the Specification:

Immediately after the title, please insert the following paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS:

This application is the National Stage of International Application No. PCT/JP2005/003903, filed March 7, 2005, which claims the benefit of Japanese Application No. 2004-063016, filed March 5, 2004 and Japanese Application No. 2004-170424, filed June 8, 2004, the contents of which are incorporated by reference herein.

Please replace the second paragraph on page 58, with the following amended paragraph:

The obtained positive resist composition 2 was used to form a resist pattern. An organic anti-reflection coating composition "AR-19" (trade name, by Shipley) was first applied onto a silicon wafer using a spinner, and dried by calcinations on a hot plate at 215 degrees C for 60 seconds to form an organic anti-reflection coating film having a thickness of 82 nm. The obtained positive-type resist composition 1 2 was then applied onto the anti-reflection coating film using a spinner, and dried by prebake on a hot plate at 110 degrees C for 90 seconds to form a resist layer having a thickness of 150 nm on the anti-reflection coating film. Next, the resist layer was selectively irradiated through a mask pattern with an ArF excimer laser (193 nm) by means of an exposure system (NSR-S302B, by Nikon Corporation; NA (numerical aperture)=0.60, 2/3 annular illumination). In simulated immersion lithography treatment, when rotating the silicon wafer having the resist layer exposed, pure water was allowed to drip onto the resist layer at 23 degrees C for 2 minutes. Subsequently, the resist layer was subjected to PEB treatment at 110 degrees C for 90 seconds, and subjected to development using an alkaline developer solution at 23 degrees C for 60 seconds. As the alkaline developer solution, a 2.38 mass% tetramethylammonium hydroxide water solution was used.